

## Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N2219AJ)
- JANTX level (2N2219AJX)
- JANTXV level (2N2219AJV)
- JANS level (2N2219AJS)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV and JANS
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations  
[www.SEMICOA.com](http://www.SEMICOA.com) or (714) 979-1900

## Applications

- General purpose
- Low power
- NPN silicon transistor



## Features

- Hermetically sealed TO-39 metal can
- Also available in chip configuration
- Chip geometry 0400
- Reference document: MIL-PRF-19500/251

## Benefits

- Qualification Levels: JAN, JANTX, JANTXV and JANS
- Radiation testing available

<b>Absolute Maximum Ratings</b>		$T_c = 25^\circ\text{C}$ unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	50	Volts
Collector-Base Voltage	$V_{CBO}$	75	Volts
Emitter-Base Voltage	$V_{EBO}$	6	Volts
Collector Current, Continuous	$I_C$	800	mA
Power Dissipation, $T_A = 25^\circ\text{C}$ Derate linearly above $25^\circ\text{C}$	$P_T$	0.8 4.6	W mW/ $^\circ\text{C}$
Power Dissipation, $T_c = 25^\circ\text{C}$ Derate linearly above $25^\circ\text{C}$	$P_T$	3.0 17.0	W mW/ $^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +200	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to +200	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS**

 characteristics specified at  $T_A = 25^\circ\text{C}$ 
**Off Characteristics**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = 10 \text{ mA}$	50			Volts
Collector-Base Cutoff Current	$I_{\text{CBO}1}$	$V_{\text{CB}} = 75 \text{ Volts}$			10	$\mu\text{A}$
Collector-Base Cutoff Current	$I_{\text{CBO}2}$	$V_{\text{CB}} = 60 \text{ Volts}$			10	nA
Collector-Base Cutoff Current	$I_{\text{CBO}3}$	$V_{\text{CB}} = 60 \text{ Volts}, T_A = 150^\circ\text{C}$			10	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{\text{CES}}$	$V_{\text{CE}} = 50 \text{ Volts}$			10	nA
Emitter-Base Cutoff Current	$I_{\text{EBO}1}$	$V_{\text{EB}} = 6 \text{ Volts}$			10	$\mu\text{A}$
Emitter-Base Cutoff Current	$I_{\text{EBO}2}$	$V_{\text{EB}} = 4 \text{ Volts}$			10	nA

**On Characteristics**

 Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{\text{FE}1}$	$I_C = 0.1 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$	30		325	
	$h_{\text{FE}2}$	$I_C = 1.0 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$	75			
	$h_{\text{FE}3}$	$I_C = 10 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$	100			
	$h_{\text{FE}4}$	$I_C = 150 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$	100		300	
	$h_{\text{FE}5}$	$I_C = 500 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$	30			
	$h_{\text{FE}6}$	$I_C = 10 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $T_A = -55^\circ\text{C}$	35			
Base-Emitter Saturation Voltage	$V_{\text{BEsat}1}$ $V_{\text{BEsat}2}$	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.6		1.2 2.0	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CEsat}1}$ $V_{\text{CEsat}2}$	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$			0.3 1.0	Volts

**Dynamic Characteristics**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{\text{FE}} $	$V_{\text{CE}} = 20 \text{ Volts}, I_C = 20 \text{ mA}, f = 100 \text{ MHz}$	2.5		12	
Small Signal Short Circuit Forward Current Transfer Ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 10 \text{ Volts}, I_C = 1 \text{ mA}, f = 1 \text{ kHz}$	75			
Open Circuit Output Capacitance	$C_{\text{OBO}}$	$V_{\text{CB}} = 10 \text{ Volts}, I_E = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			8	pF
Open Circuit Input Capacitance	$C_{\text{IBO}}$	$V_{\text{EB}} = 0.5 \text{ Volts}, I_C = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			25	pF

**Switching Characteristics**

Saturated Turn-On Time	$t_{\text{ON}}$				35	ns
Saturated Turn-Off Time	$t_{\text{OFF}}$				300	ns

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